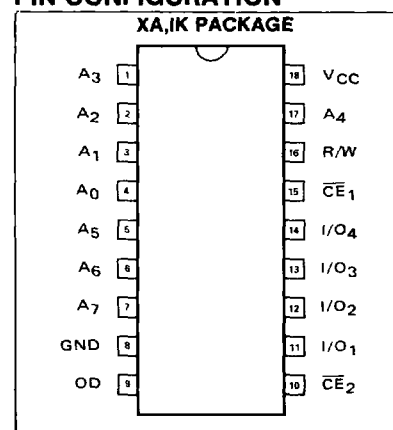
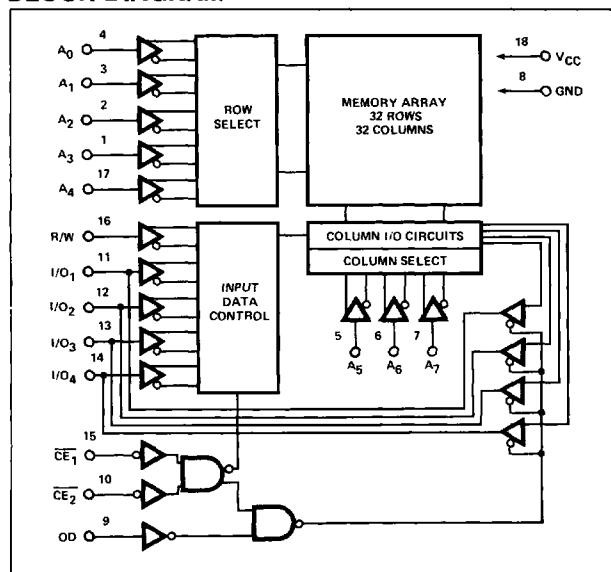


DESCRIPTION

The 2111 series are 1024-bit high performance, low power static read/write RAMS organized as 256 words by 4 bits.

The 2111 series are fully static and no refresh operations, sense amplifiers, or clocks are required. All inputs and outputs are directly TTL-compatible and only one +5V power supply is required.

The 2111 series is fabricated with N-channel silicon gate technology which allows the design of high performance easy to use MOS circuits and provides a high functional density on a given monolithic chip.

PIN CONFIGURATION**BLOCK DIAGRAM****SWITCHING CHARACTERISTICS**

$T_A = 0^\circ\text{C}$ to 70°C , $V_{CC} = 5\text{V} \pm 5\%$, unless otherwise specified.

READ CYCLE			2111		2111-1		2111-2		2611		Unit
Parameter	Test Conditions		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
t_{RC} Read Cycle			1,000		500		650		400		ns
t_A Access Time	$t_r, t_f = 20\text{ns}$			1,000		500		650		400	ns
t_{CC} Chip Enable To Output	$V_{IN} = +0.65\text{V}$ to $+2.2\text{V}$			800		350		400		175	ns
t_{OD} Output Disable To Output	Timing Reference = 1.5V			700		300		350		150	ns
$t_{DF}^{(3)}$ Data Output to High Z State	Load = 1 TTL Gate		0	200	0	150	0	150		125	ns
t_{OH} Previous Read Data Valid after change of Address	and $C_L = 100\text{pF}$.		40		40		40		40		ns
WRITE CYCLE			2111		2111-1		2111-2		2611		Unit
Parameter	Test Conditions		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
t_{WC} Write Cycle			1,000		500		650		400		ns
t_{AW} Write Delay	$t_r, t_f = 20\text{ns}$		150		100		150			400	ns
t_{CW} Chip Enable To Write	$V_{IN} = +0.65\text{V}$ to $+2.2\text{V}$		900		400		550		150		ns
t_{DW} Data Setup	Timing Reference = 1.5V		700		280		400		125		ns
t_{DH} Data Hold	Load = 1 TTL Gate		100		100		100		50		ns
t_{WP} Write Pulse	and $C_L = 100\text{pF}$.		750		300		400		150		ns
t_{WR} Write Recovery			50		50		50		0		ns
t_{DS} Output Disable Setup			200		150		150		150		ns

